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**Two-Dimensional Oxide Topological Insulator With LiFeAs Structure** QIUNAN XU, ZHIDA SONG, SIMIN NIE, HONGMING WENG, ZHONG FANG, XI DAI, Chinese Academy of Sci (CAS), KEY LABORA-TORY OF CONDENSED MATTER THEORY AND COMPUTATION, CHINESE ACADEMY OF SCI, T03 GROUP TEAM — Using first-principles calculations, we propose that ZrSiO can be viewed as a three-dimensional (3D) oxide weak topological insulator (TI) with  $Z_2$  idiocies (0; 001). Further calculations show that the single layer of such material is a long-sought-after 2D oxide TI with a band gap around 10 meV. Furthermore, we also find that there are many other isostructural compounds, which can host similar electronic structure and form a 'WHM' material family with 'W' being Zr, Hf or La, 'H' being group IV or group V element, and 'M' being group VI one.

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